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(71) Applicant (for all designated States except US): **KONINKLIJKE PHILIPS ELECTRONICS N.V.** [NL/NL];
Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **HERINGA, Anco**

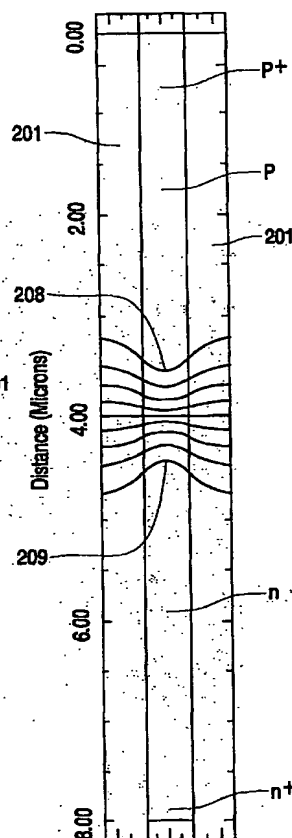
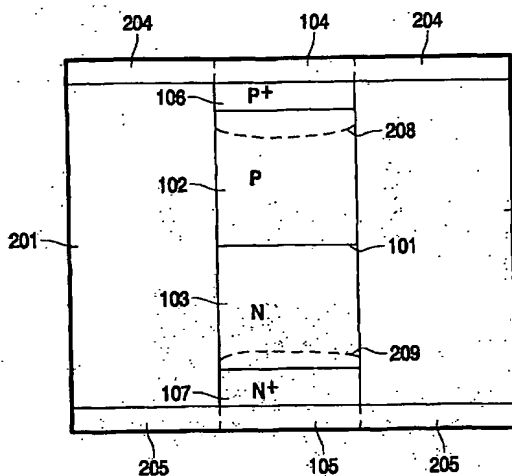
[NL/NL]; c/o Philips Intellectual Property & Standards,
Cross Oak Lane, Redhill Surrey RH1 5HA (GB). **HUETING, Raymond, J., E.** [NL/GB]; c/o Philips Intellectual
Property & Standards, Cross Oak Lane, Redhill Surrey
RH1 5HA (GB). **SLOTBOOM, Jan, W.** [NL/NL]; c/o
Philips Intellectual Property & Standards, Cross Oak Lane,
Redhill Surrey RH1 5HA (GB).

(74) Agent: **WILLIAMSON, Paul, L.**; c/o Philips Intellectual
Property & Standards, Cross Oak Lane, Redhill Surrey
RH1 5HA (GB).

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(54) Title: SEMICONDUCTOR DEVICES WITH A FIELD SHAPING REGION



(57) Abstract: A semiconductor device, for example a diode (200), having a pn junction (101) has an insulating material field shaping region (201) adjacent, and possibly bridging, the pn junction. The field shaping region (201) preferably has a high dielectric constant and is coupled via capacitive voltage coupling regions (204,205) to substantially the same voltages as are applied to the pn junction. When a reverse voltage is applied across the pn junction (101) and the device is non-conducting, a capacitive electric field, is present in a part of the field shaping region which extends beyond a limit of the pn junction depletion region which would exist in the absence of the field shaping region (201), the electric field in the field shaping region inducing a stretched electric field limited to a correspondingly stretched pn junction depletion region (208,209) and an increased reverse breakdown voltage of the device.

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